

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A fabrication method for integrating a plurality of heterogeneous circuit devices in a single substrate, comprising:

providing a substrate;

forming a first protective layer over the substrate;

removing a portion of the first protective layer to expose a first portion of the substrate;

ion implanting a high voltage well of a first circuit device in the first portion of the substrate using the partially removed first protective layer;

forming a second protective layer over at least the first portion of the substrate;

removing a second portion of the ~~second~~ first protective layer to expose a second portion of the substrate; and

ion implanting a first low voltage well of a second circuit device in the second portion of the substrate using the partially removed first protective layer and the second protective layer.
